

IRS2113MPBF HIGH- AND LOW-SIDE DRIVER

Features

- Floating channel designed for bootstrap operation
- Fully operational to +600 V
- Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 10 V to 20 V
- Undervoltage lockout for both channels
- 3.3 V input logic compatible
- Separate logic supply range from 3.3 V to 20 V
- Logic and power ground ±5 V offset
- CMOS Schmitt-triggered inputs with pull-down
- Cycle by cycle edge-triggered shutdown logic
- Matched propagation delay for both channels
- Output in phase with inputs
- · Leadfree, RoHS Compliant

Description

The IRS2113MPBF is a high voltage, high speed power MOSFET and IGBT drivers with independent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3 V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. Propagation delays are matched to simplify use in high frequency applications. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 V.

Product Summary

Topology	2 channels
V _{OFFSET}	600 V max
V _{OUT}	10 V – 20 V
I _{o+} & I _{o-} (typical)	2.5 A / 2.5 A
t _{ON} & t _{OFF} (typical)	130 ns & 120 ns
Delay Matching	20 ns max

Package Option



Typical Connection Diagram Up to 600V НО V_{DD} V_{DD} O V_{B} HIN O-HIN V_{S} О то SD ()-SD LOAD
 . V_{CC} LIN LIN O Vss O СОМ V_{ss} $V_{cc} \bigcirc$ LO



Qualification Information[†]

			Industrial ^{††} (per JEDEC JESD 47)		
Qualification Level		Comments: This IC has passed JEDEC's Industria			
		qualification. IR's Cor	nsumer qualification level is		
		granted by extension of	f the higher Industrial level.		
			MSL2 ^{†††}		
Moisture Sensitivity Level		MLPQ4x4 14L	(per IPC/JEDEC J-STD-		
			020)		
	Machine Model	Class A (+/-200V)			
	Machine Model	(per JEDEC standard JESD22-A115)			
ESD	Human Body Model	Class 1B (+/-1000V)			
LSD	Tiuman Body Woder	(per EIA/JEDEC standard EIA/JESD22-A114)			
	Charged Davies Model	Class III (+/-1000V)			
Charged Device Model		(per JEDEC standard JESD22-C101)			
IC Latch-Up Test	IC Latabilin Tast		Class II, Level A		
ic Lateri-op rest	ic Laten-op rest		(per JESD78A)		
RoHS Compliant	·	Yes			

- † Qualification standards can be found at International Rectifier's web site http://www.irf.com/
- †† Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information.
- ††† Higher MSL ratings may be available for the specific package types listed here. Please contact your International Rectifier sales representative for further information.



Absolute Maximum Ratings

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units
V_B	High-side floating supply voltage	-0.3	625	
Vs	High-side floating supply offset voltage	V _B - 20	V _B + 0.3	
V_{HO}	High-side floating output voltage	V _S - 0.3	V _B + 0.3	
V_{CC}	Low-side fixed supply voltage	-0.3	25	V
V_{LO}	Low-side output voltage	-0.3	V _{CC} + 0.3	•
V_{DD}	Logic supply voltage	-0.3	V _{SS} + 20 (†)	
V_{SS}	Logic supply offset voltage	V _{CC} - 20	V _{CC} + 0.3	
V_{IN}	Logic input voltage (HIN, LIN & SD)	V _{SS} -0.3	$V_{DD} + 0.3$	
dV _S /dt	Allowable offset supply voltage transient (Fig. 2)	_	50	V/ns
P_D	Package power dissipation @ TA ≤ 25°C	_	2.08	W
Rth _{JA}	Thermal resistance, junction to ambient	_	36	°C/W
TJ	Junction temperature	_	150	
Ts	Storage temperature	-55	150	°C
T_L	Lead temperature (soldering, 10 seconds)	_	300	

[†] All supplies are fully tested at 25 V, and an internal 20 V clamp exists for each supply.

Recommended Operating Conditions

The input/output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. The $V_{\rm S}$ and $V_{\rm SS}$ offset rating are tested with all supplies biased at 15 V differential.

Symbol	Definition	Min.	Max.	Units
V_{B}	High-side floating supply absolute voltage	V _S +10	V _S +20	
Vs	High-side floating supply offset voltage	†	600	
V_{HO}	High-side floating output voltage	Vs	V_{B}	
V_{CC}	Low-side fixed supply voltage	10	20	V
V_{LO}	Low-side output voltage	0	V_{CC}	v
V_{DD}	Logic supply voltage	V _{SS} + 3	V _{SS} + 20	
V_{SS}	Logic ground offset voltage	-5 (††)	5	
V_{IN}	Logic input voltage (HIN, LIN & SD)	V_{SS}	V_{DD}	
T_A	Ambient temperature	-40	125	°C

[†] Logic operational for V_S of -4 V to +500 V. Logic state held for V_S of -4 V to – V_{BS} . (Please refer to the Design Tip DT97 -3 for more details).

^{††} When V_{DD} < 5 V, the minimum V_{SS} offset is limited to $-V_{DD}$.



Static Electrical Characteristics

 V_{BIAS} (V_{CC} , V_{BS} , V_{DD}) = 15 V, T_A = 25°C and V_{SS} = COM unless otherwise specified. The V_{IL} , V_{TH} and I_{IN} parameters are referenced to V_{SS} and are applicable to all three logic input leads: HIN, LIN and SD. The V_{O} , and I_{O} parameters are referenced to COM and are applicable to the respective output leads: HO or LO.

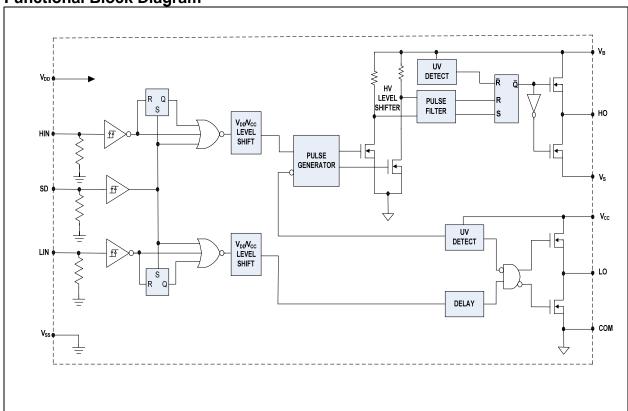
Symbol	Definition	Min	Тур	Max	Units	Test Conditions
V_{IH}	Logic "1" input voltage	9.5	_	_		
V_{IL}	Logic "0" input voltage	_	_	6.0	V	
V _{OH}	High level output voltage, V _{BIAS} - V _O	_	_	1.4	V	$I_O = 0 A$
V_{OL}	Low level output voltage, Vo	_	_	0.15		I _O = 20 mA
I _{LK}	Offset supply leakage current	_		50		$V_{\rm B} = V_{\rm S} = 600$
I_{QBS}	Quiescent V _{BS} supply current	_	125	230)/ 0)/ an
I _{QCC}	Quiescent V _{CC} supply current	_	180	340	μΑ	$V_{IN} = 0 V \text{ or } V_{DD}$
I_{QDD}	Quiescent V _{DD} supply current	_	15	30		V DD
I _{IN+}	Logic "1" input bias current	_	20	40		$V_{IN} = V_{DD}$
I _{IN-}	Logic "0" input bias current	_	_	5.0		$V_{IN} = 0 V$
V_{BSUV}	V _{BS} supply undervoltage positive going threshold	7.5	8.6	9.7		
V_{BSUV}	V _{BS} supply undervoltage negative going threshold	7.0	8.2	9.4	V	
$V_{\text{CCUV+}}$	V _{CC} supply undervoltage positive going threshold	7.4	8.5	9.6	V	
V _{CCUV-}	V _{CC} supply undervoltage negative going threshold	7.0	8.2	9.4		
I _{O+}	Output high short circuit pulsed current	2.0	2.5	_	Α	$V_O = 0 V$, $V_{IN} = V_{DD}$ $PW \le 10 \text{ us}$
I _{O-}	Output low short circuit pulsed current	2.0	2.5		A	$V_O = 15 V$, $V_{IN} = 0 V$ $PW \le 10 us$

Dynamic Electrical Characteristics

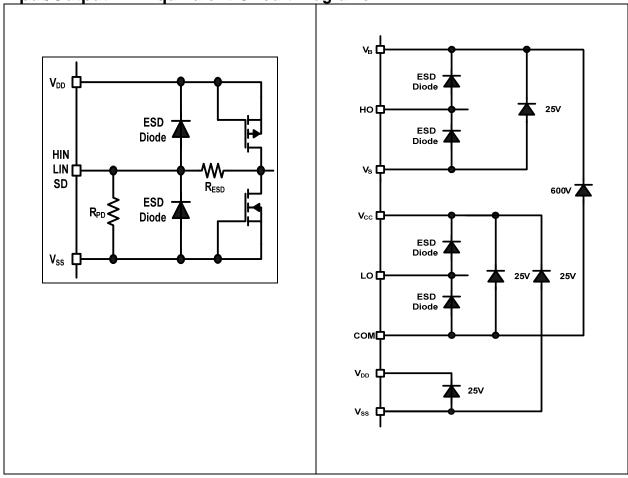
 V_{BIAS} (V_{CC} , V_{BS} , V_{DD}) = 15 V, C_{L} = 1000 pF, T_{A} = 25°C and V_{SS} = COM unless otherwise specified. The dynamic electrical characteristics are measured using the test circuit shown in Fig. 3.

Symbol	Definition	Min	Тур	Max	Units	Test Conditions
t_{on}	Turn-on propagation delay		130	200		$V_S = 0 V$
t_{off}	Turn-off propagation delay		120	190		V _S = 600 V
t_{sd}	Shutdown propagation delay	_	130	160	ns	V _S = 000 V
t _r	Turn-on rise time		25	35	113	
t_f	Turn-off fall time	_	17	25		
MT	Delay matching, HS & LS turn on/off		_	20		

Functional Block Diagram



Input/Output Pin Equivalent Circuit Diagrams

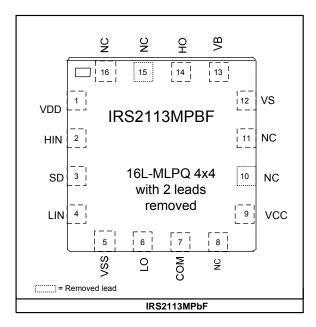




Lead Definitions

PIN	Symbol	Description		
1	V_{DD}	Logic supply		
2	HIN	Logic input for high-side gate driver output (HO), in phase		
3	SD	Logic input for shutdown		
4	LIN	Logic input for low-side gate driver output (LO), in phase		
5	V_{SS}	Logic ground		
6	LO	Low-side gate drive output		
7	COM	Low-side return		
8	NC	No Connection		
9	V_{CC}	Low-side supply		
10	NC	No Connection (pin removed)		
11	NC	No Connection		
12	V_S	High-side floating supply return		
13	V_{B}	High-side floating supply		
14	НО	High-side gate drive output		
15	NC	No Connection (pin removed)		
16	NC	No Connection		

Lead Assignments



Application Information and Additional Details

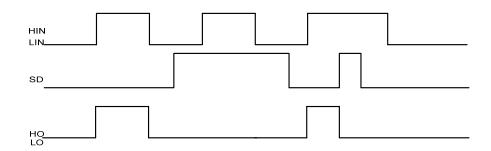


Figure 1: Input/Output Timing Diagram

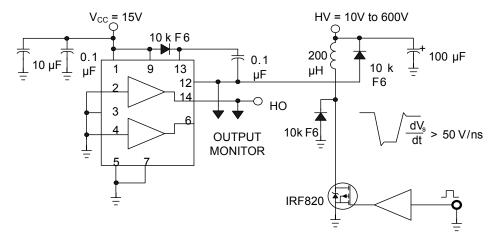


Figure 2: Floating Supply Voltage Transient Test Circuit

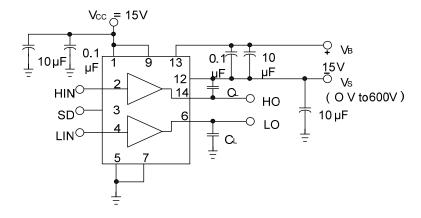


Figure 3: Switching Time Test Circuit

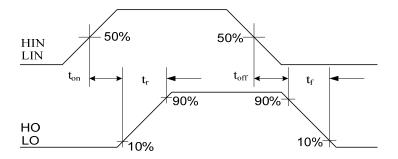


Figure 4: Switching Time Waveform Definitions

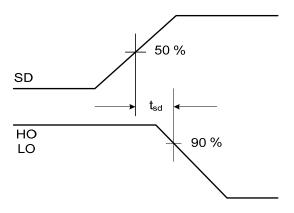


Figure 5: Shutdown Waveform Definitions

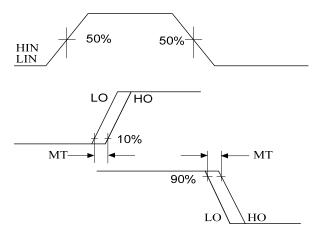
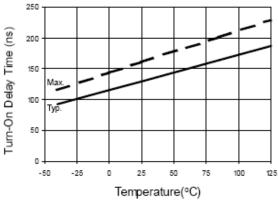


Figure 6: Delay Matching Waveform Definitions

Parameter Temperature Trends



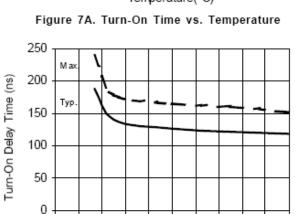


Figure 7C. Turn-On Time vs. VDD Supply Voltage

V_{DD} Supply Voltage (V)

10 12 14 16 18 20

6 8

2

0

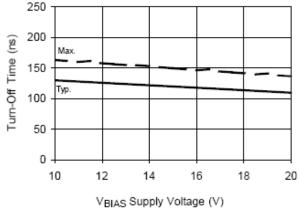


Figure 8B. Turn-Off Time vs. Supply Voltage

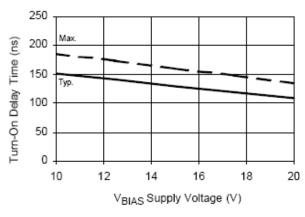


Figure 7B. Turn-On Time vs. Supply Voltage

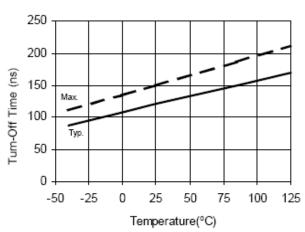


Figure 8A. Turn-Off Time vs. Temperature

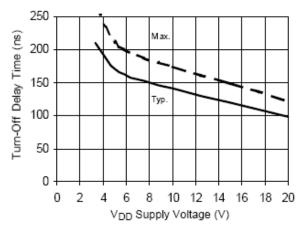


Figure 8C. Turn-Off Time vs. VDD Supply Voltage

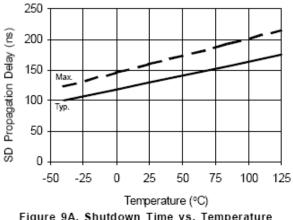


Figure 9A. Shutdown Time vs. Temperature

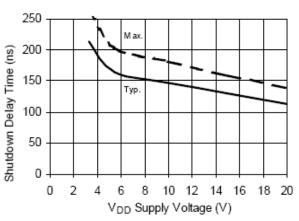


Figure 9C. Shutdown Time vs. VDD Supply Voltage

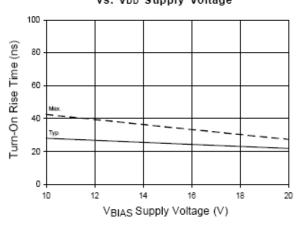
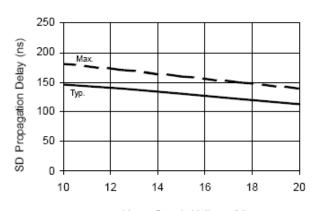


Figure 10B. Turn-On Rise Time vs. Voltage



VBIAS Supply Voltage (V) Figure 9B. Shutdown Time vs. Supply Voltage

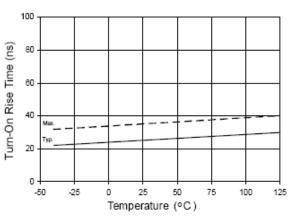


Figure 10A. Turn-On Rise Time vs. Temperature

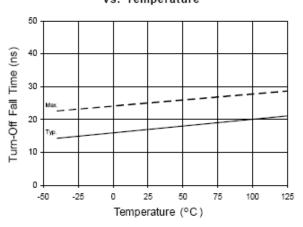


Figure 11A. Turn-Off Fall Time vs. Temperature

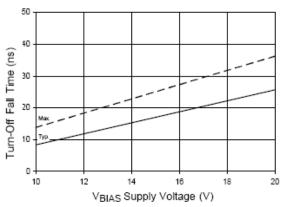


Figure 11B. Turn-Off Fall Time vs. Voltage

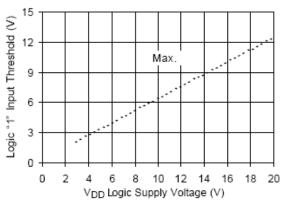


Figure 12B. Logic "1" Input Threshold vs. Voltage

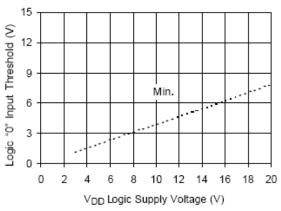


Figure 13B. Logic "0" Input Threshold vs. Voltage

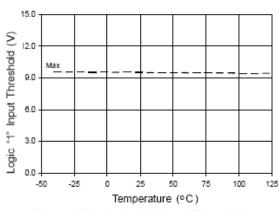


Figure 12A. Logic "1" Input Threshold vs. Temperature

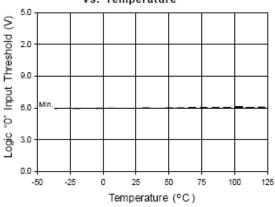


Figure 13A. Logic "0" Input Threshold vs. Temperature

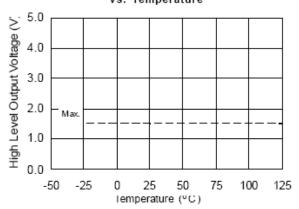


Figure 14A. High Level Output Voltage vs. Temperature (I_O = 0 mA)

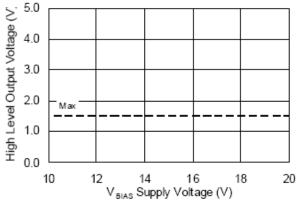


Figure 14B. High Level Output Voltage vs. Supply Voltage (I_O = 0 mA)

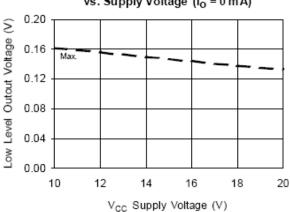


Figure 15B. Low Level Output vs. Supply Voltage

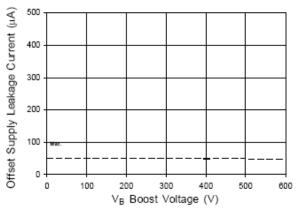


Figure 16B. Offset Supply Current vs. Voltage

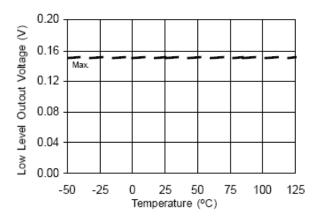


Figure 15A. Low Level Output vs. Temperature

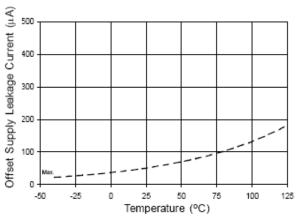


Figure 16A. Offset Supply Current vs. Temperature

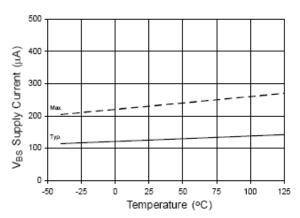


Figure 17A. VBs Supply Current vs. Temperature

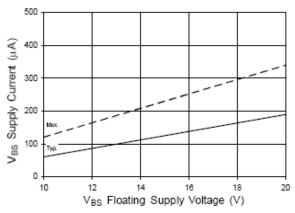


Figure 17B. V_{BS} Supply Current vs. Voltage

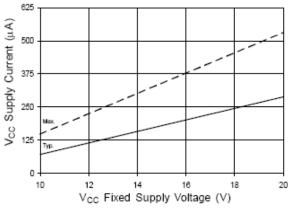


Figure 18B. Vcc Supply Current vs. Voltage

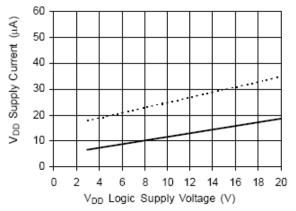


Figure 19B. V_{DD} Supply Current vs. V_{DD} Voltage

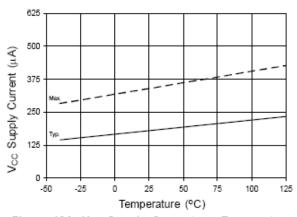


Figure 18A. Vcc Supply Current vs. Temperature

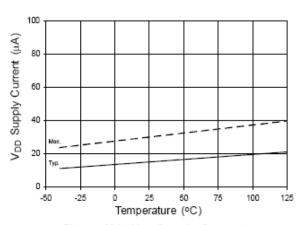


Figure 19A. V_{DD} Supply Current vs. Temperature

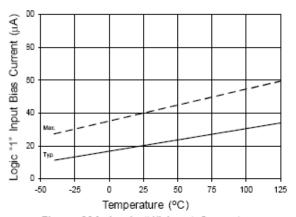


Figure 20A. Logic "1" Input Current vs. Temperature

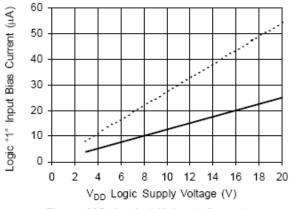


Figure 20B. Logic "1" Input Current vs. Vod Voltage

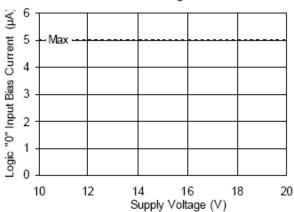


Figure 21B. Logic "0" Input Bias Current vs. Voltage

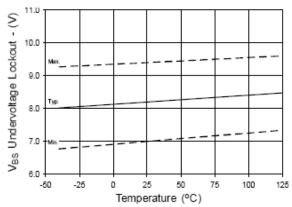


Figure 23. V_{BS} Undervoltage (-) vs. Temperature

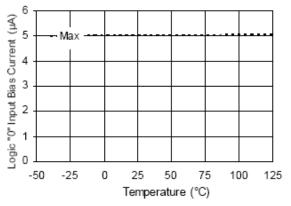


Figure 21A. Logic "0" Input Bias Current

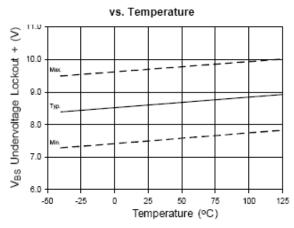


Figure 22. VBs Undervoltage (+) vs. Temperature

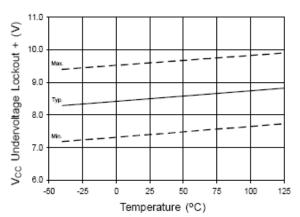


Figure 24. V_{CC} Undervoltage (+) vs. Temperature

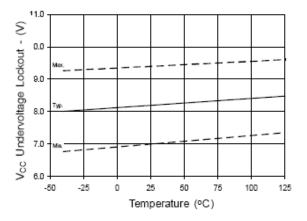


Figure 25. Vcc Undervoltage (-) vs. Temperature

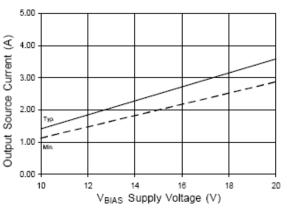


Figure 26B. Output Source Current vs. Voltage

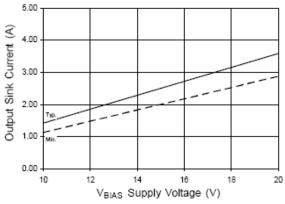


Figure 27B. Output Sink Current vs. Voltage

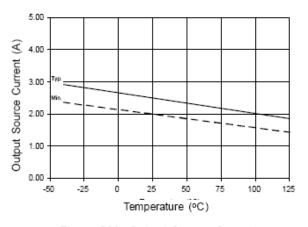


Figure 26A. Output Source Current vs. Temperature

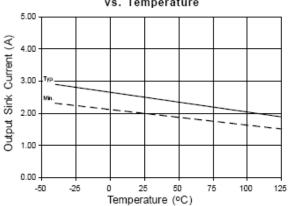


Figure 27A. Output Sink Current vs. Temperature

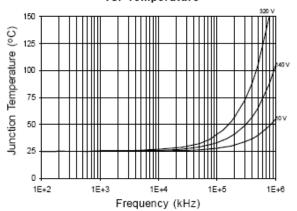


Figure 28. IRS2110/IRS2113 T_J vs. Frequency (IRFBC20) $R_{GATE} = 33 \Omega$, $V_{CC} = 15 V$

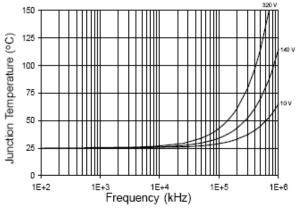


Figure 29. IRS2110/IRS2113 T_J vs. Frequency (IRFBC30) R_{GATE} = 22Ω , V_{CC} = 15 V

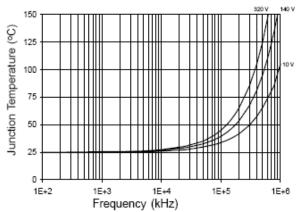


Figure 31. IRS2110/IRS2113 T_J vs. Frequency (IRFPE50) R_{GATE} = 10Ω , V_{CC} = 15 V

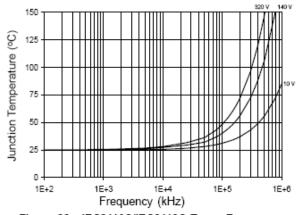


Figure 33. IRS2110S/IRS2113S T_J vs. Frequency (IRFBC30) R_{GATE} = 22Ω , V_{CC} = 15 V

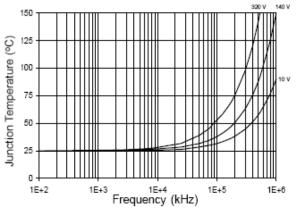


Figure 30. IRS2110/IRS2113 T_J vs. Frequency (IRFBC40) R_{GATE} = 15Ω , V_{CC} = 15 V

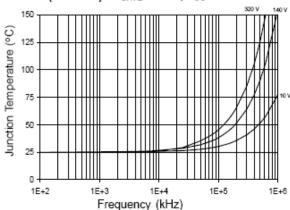


Figure 32. IRS2110S/IRS2113S T_J vs. Frequency (IRFBC20) R_{GATE} = 33 Ω , V_{CC} = 15 V

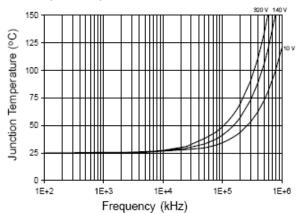


Figure 34. IRS2110S/IRS2113S T_J vs. Frequency (IRFBC40) R_{GATE} = 15 Ω , V_{CC} = 15 V

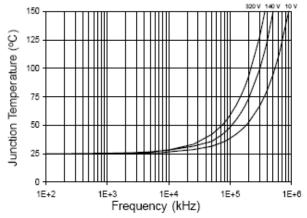


Figure 35. IRS2110S/IRS2113S T_J vs. Frequency (IRFPE50) R_{GATE} = 10Ω , V_{CC} = 15 V

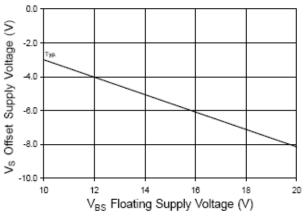


Figure 36. Maximum V_S Negative Offset vs. V_{BS} Supply Voltage

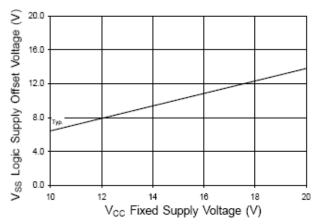
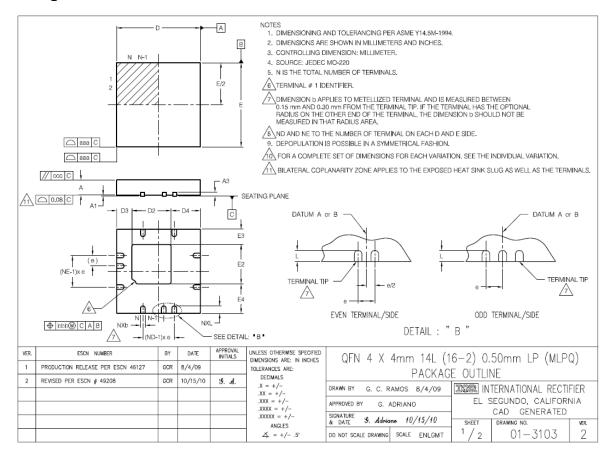


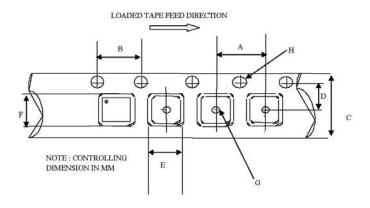
Figure 37. Maximum V_{SS} Positive Offset vs. V_{CC} Supply Voltage

Package Details: MLPQ 4x4 -16L



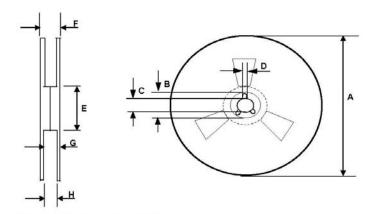
SYMBOL	VGGD-10						
B	М	ILLIMETE	ERS		INCHES		
Ľ	MIN	NOM	MAX	MIN NOM MA			
Α	0.80	0.90	1.00	0 .032 .035 .0			
A1	0.00	0.02	0.05	.000	.0008	.0019	
A3		0.20 REF	F		.008 REF		
b	0.18	0.25	0.30	.007	.010	.012	
D2	1.78	1.88	1.98	.070	.074	.078	
D3		0.73 REF	F		.029 REF		
D4		1.40 REF	F		.055 REF		
D		4.00 BS0	0	.157 BSC			
Е		4.00 BS0	0		.157 BSC		
E4		0.73 REF	F		.029 REF		
E3		1.40 REF	F		.055 REF		
E2	1.78	1.88	1.98	.070	.074	.078	
L	0.30	0.40	0.50	.012	.016	.020	
е	(0.50 PITC	Н	.(20 PITC	Н	
Ν		16			16		
ND	4				4		
NE	4				4		
aaa	0.15				.0059		
bbb	0.10				.0039		
ccc		0.10			.0039		
ddd		0.05			.0019		

Tape and Reel Details: MLPQ 4x4



CARRIER TAPE DIMENSION FOR MLPQ4X4V

	Metric		Imp	erial
Code	Min	Max	Min	Max
Α	7.90	8.10	0.311	0.358
В	3.90	4.10	0.154	0.161
B C	11.70	12.30	0.461	0.484
D	5.45	5.55	0.215	0.219
E	4.25	4.45	0.168	0.176
E F	4.25	4.45	0.168	0.176
G	1.50	n/a	0.059	n/a
Н	1.50	1.60	0.059	0.063

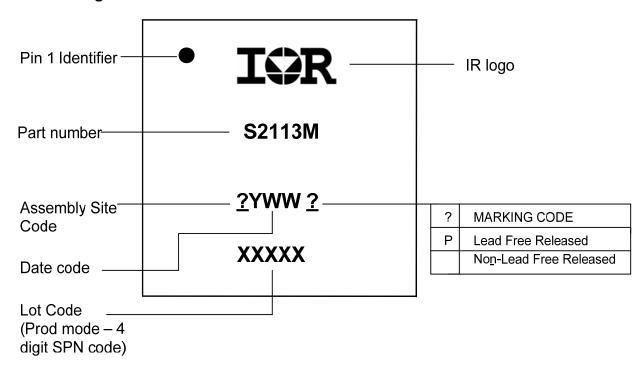


REEL DIMENSIONS FOR MLPQ4X4V

	Me	tric	Imp	erial
Code	Min	Max	Min	Max
A	329.60	330.25	12.976	13.001
В	20.95	21.45	0.824	0.844
С	12.80	13.20	0.503	0.519
D	1.95	2.45	0.767	0.096
E	98.00	102.00	3.858	4.015
F	n/a	18.40	n/a	0.724
G	14.50	17.10	0.570	0.673
G H	12.40	14.40	0.488	0.566



Part Marking Information:



Ordering Information

		Standard	Pack	
Base Part Number	Package Type	Form	Quantity	Complete Part Number
	MI DO 4v4 461	Tube/Bulk	92	IRS2113MPBF
IRS2113	MLPQ 4x4-16L	Tape and Reel	3,000	IRS2113MTRPBF

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For technical support, please contact IR's Technical Assistance Center http://www.irf.com/technical-info/

WORLD HEADQUARTERS:

233 Kansas St., El Segundo, California 90245 Tel: (310) 252-7105 **Revision History**

110110101111110	
Date	Comment
09/24/09	Initial conversion from SO package style data sheet
03/24/2010	Included qual info page
11/19/2010	Updated POD